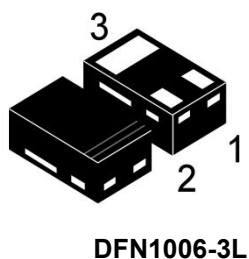


MMBT3904NC

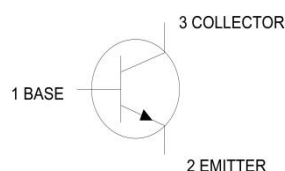
Feature

- Switching Transistor
- Collector-emitter voltage $V_{CE}=40V$
- Collector current $I_C=0.2A$

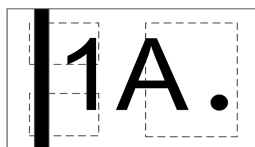
Package



Circuit diagram



Marking



Absolute maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

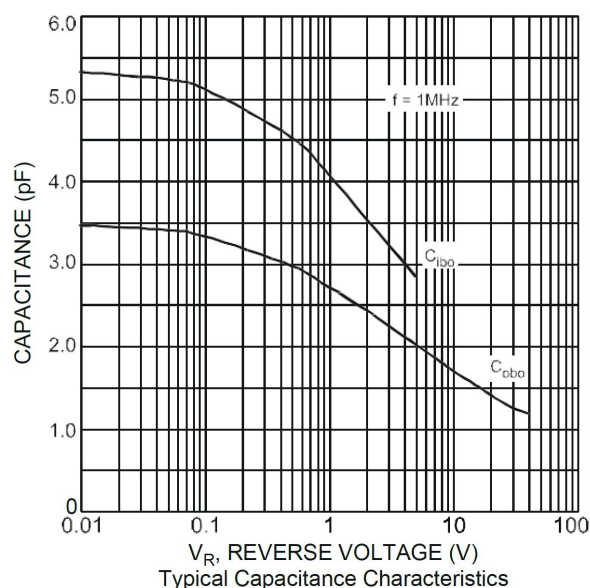
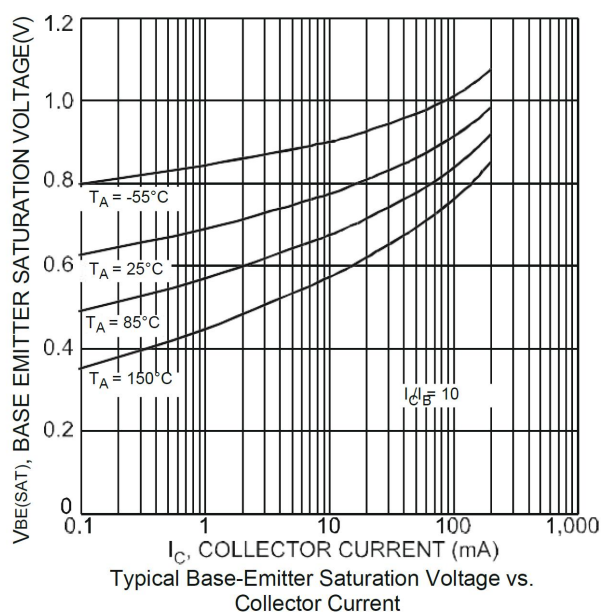
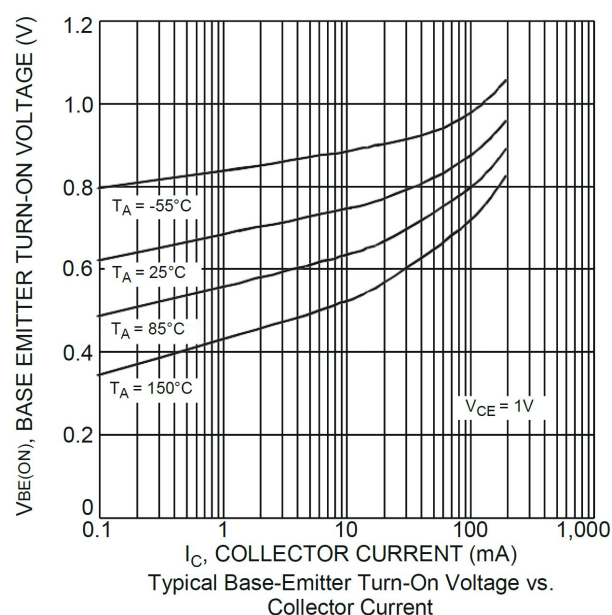
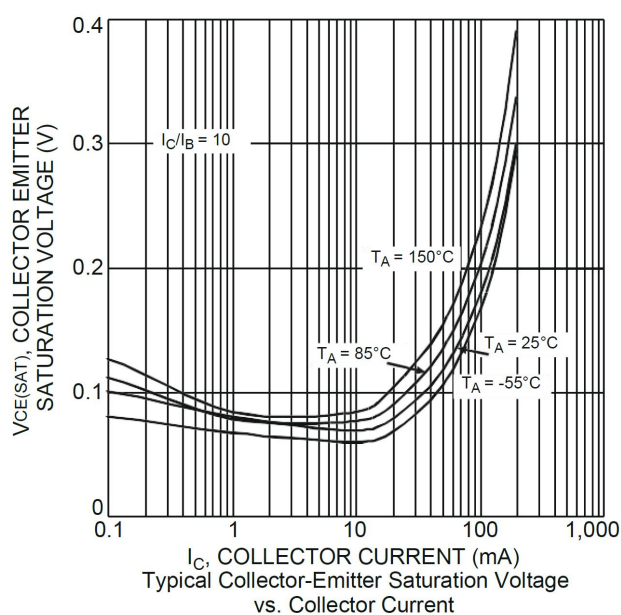
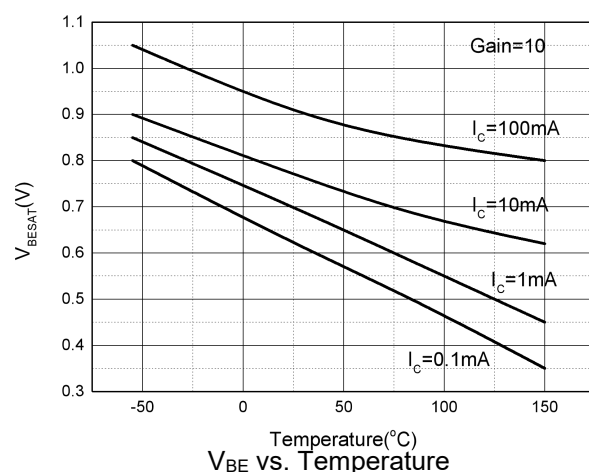
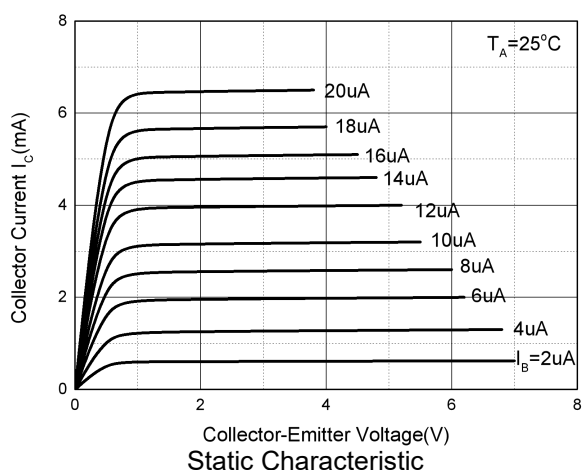
Parameter	Symbol	Value	Unit
Collector Emitter Voltage	V_{CEO}	40	V
Collector Base Voltage	V_{CBO}	60	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Power Dissipation	P_{tot}	100	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}C$

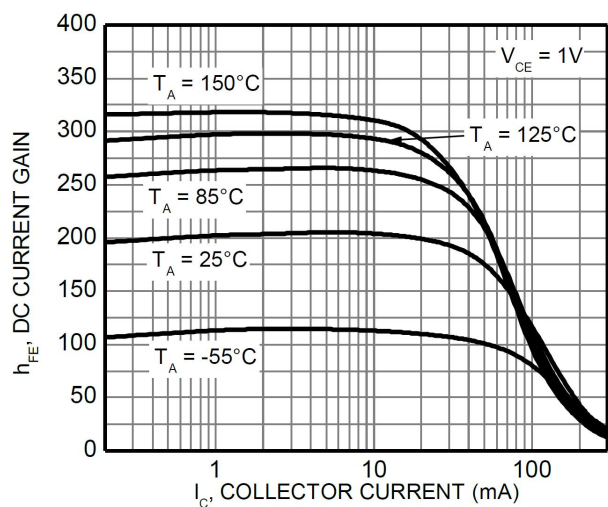
Electrical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=1\text{mA}$, $I_B=0$	40		V
Collector-base breakdown voltage	BV_{CBO}	$I_C=10\mu\text{A}$, $I_E=0$	60		V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=10\mu\text{A}$, $I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$		100	nA
Collector cut-off current	I_{CEO}	$V_{CE}=40\text{V}$, $I_B=0$		5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}$, $I_C=0$		100	nA
DC current gain	h_{FE}	$V_{CE}=1\text{V}$, $I_C=10\text{mA}$	100	400	
		$V_{CE}=1\text{V}$, $I_C=0.1\text{mA}$	40		
		$V_{CE}=1\text{V}$, $I_C=1\text{mA}$	70		
		$V_{CE}=1\text{V}$, $I_C=100\text{mA}$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$		0.2	V
		$I_C=50\text{mA}$, $I_B=5\text{mA}$		0.3	
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$	0.65	0.85	V
		$I_C=50\text{mA}$, $I_B=5\text{mA}$		0.95	
Transition frequency	f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	300		MHZ
Output Capacitance	C_{obo}	$V_{CB}=5.0\text{Vdc}$, $I_E=0$, $f=1.0\text{MHz}$		4	pF
Input Capacitance	C_{ibo}	$V_{EB}=0.5\text{Vdc}$, $I_E=0$, $f=1.0\text{MHz}$		8	pF
Delay Time	T_d	$V_{CC}=3.0\text{Vdc}$, $V_{BE}=-0.5\text{Vdc}$, $I_C=10\text{mA}$		35	ns
Rise Time	T_r	$I_B=1.0\text{mA}$		35	
Storage Time	T_s	$V_{CC}=3.0\text{Vdc}$, $I_C=10\text{mA}$		200	
Fall Time	T_f	$I_B=I_{B2}=1.0\text{mA}$		50	

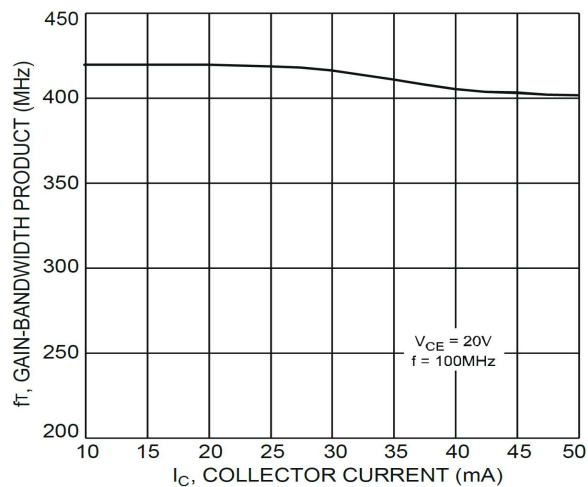


Typical Characteristics





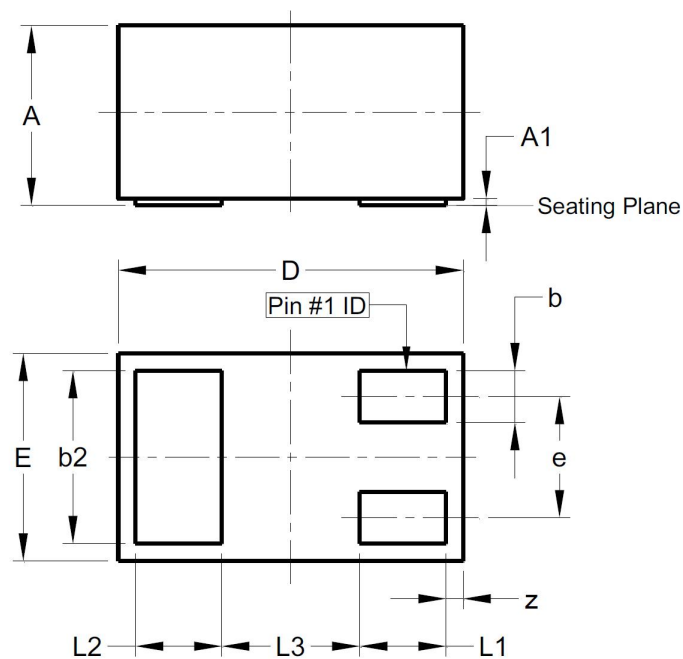
Typical DC Current Gain vs. Collector Current



Typical Gain-Bandwidth Product vs. Emitter Current

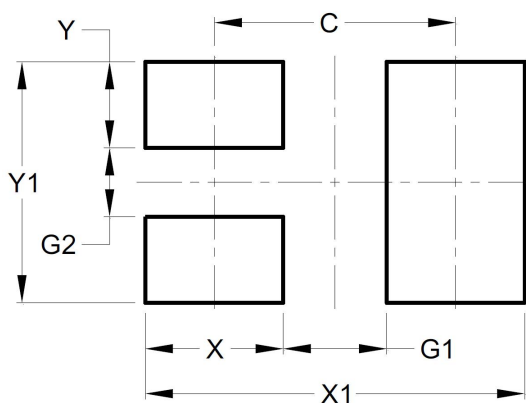


DFN1006-3L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.47	0.50	0.55
A1	0.00	-	0.05
b	0.10	0.15	0.20
b2	0.45	0.50	0.55
D	0.95	1.0	1.05
E	0.55	0.60	0.65
e	0.35BSC		
L1	0.20	0.25	0.30
L2	0.20	0.25	0.30
L3	0.40		
z	0.02	0.05	0.08

Recommend land pattern (Unit: mm)



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70